



# Rail-to-Rail Output Audio Amplifiers

## SSM2275/SSM2475\*

### FEATURES

Single or Dual-Supply Operation  
Excellent Sonic Characteristics  
Low Noise: 7 nV/ $\sqrt{\text{Hz}}$   
Low THD: 0.0006%  
Rail-to-Rail Output  
High Output Current:  $\pm 50$  mA  
Low Supply Current: 1.7 mA/Amplifier  
Wide Bandwidth: 8 MHz  
High Slew Rate: 12 V/ $\mu\text{s}$   
No Phase Reversal  
Unity Gain Stable  
Stable Parameters Over Temperature

### APPLICATIONS

Multimedia Audio  
Professional Audio Systems  
High Performance Consumer Audio  
Microphone Preamplifier  
MIDI Instruments

### GENERAL DESCRIPTION

The SSM2275 and SSM2475 use the Butler Amplifier front end, which combines both bipolar and FET transistors to offer the accuracy and low noise performance of bipolar transistors and the slew rates and sound quality of FETs. This product family includes dual and quad rail-to-rail output audio amplifiers that achieve lower production costs than the industry standard OP275 (the first Butler Amplifier offered by Analog Devices). This lower cost amplifier also offers operation from a single 5 V supply, in addition to conventional  $\pm 15$  V supplies. The ac performance meets the needs of the most demanding audio applications, with 8 MHz bandwidth, 12 V/ $\mu\text{s}$  slew rate and extremely low distortion.

The SSM2275 and SSM2475 are ideal for application in high performance audio amplifiers, recording equipment, synthesizers, MIDI instruments and computer sound cards. Where cascaded stages demand low noise and predictable performance, SSM2275 and SSM2475 are a cost effective solution. Both are stable even when driving capacitive loads.

The ability to swing rail-to-rail at the outputs (see Applications section) and operate from low supply voltages enables designers to attain high quality audio performance, even in single supply systems. The SSM2275 and SSM2475 are specified over the extended industrial ( $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ ) temperature range. The SSM2275 is available in 8-lead plastic DIPs, SOICs, and microSOIC surface-mount packages. The SSM2475 is available in narrow body SOICs and thin shrink small outline (TSSOP) surface-mount packages.

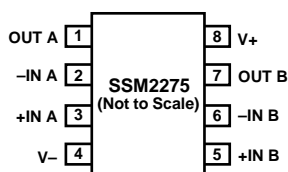
\*Protected by U.S. Patent No. 5,101,126.

### REV. A

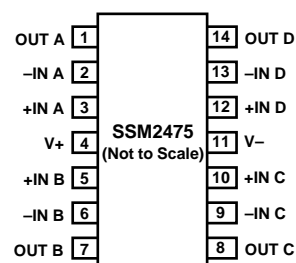
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### PIN CONFIGURATIONS

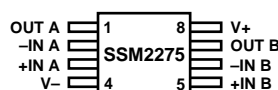
8-Lead Narrow Body SOIC  
(SO-8)



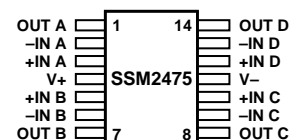
14-Lead Narrow Body SOIC  
(R-14)



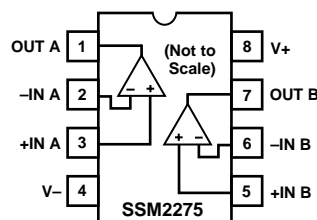
8-Lead microSOIC  
(RM-8)



14-Lead TSSOP  
(RU-14)



8-Lead Plastic DIP  
(N-8)



# SSM2275/SSM2475—SPECIFICATIONS

## ELECTRICAL CHARACTERISTICS ( $V_S = \pm 15\text{ V}$ , $T_A = +25^\circ\text{C}$ , $V_{CM} = 0\text{ V}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>INPUT CHARACTERISTICS</b>						
Offset Voltage	$V_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		1	4	mV
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		1	6	mV
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		250	400	nA
Input Voltage Range	$V_{IN}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		300	500	nA
Common-Mode Rejection Ratio	CMRR	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		5	75	nA
		$V_S = \pm 15\text{ V}$		15	125	nA
		$-12.5\text{ V} \leq V_{CM} \leq +12.5\text{ V}$	-14		+14	V
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	80	100		dB
		$-12.5\text{ V} \leq V_{CM} \leq +12.5\text{ V}$				
$A_{VO}$		$R_L = 2\text{ k}\Omega$ , $-12\text{ V} \leq V_O \leq +12\text{ V}$	80	100		V/mV
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	100	240		V/mV
			80	120		V/mV
<b>OUTPUT CHARACTERISTICS</b>						
Output Voltage, High	$V_{OH}$	$I_L \leq 20\text{ mA}$	14	14.5		V
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	14.5	14.7		V
Output Voltage, Low	$V_{OL}$	$I_L = 20\text{ mA}$		-14	-13.5	V
		$I_L = 10\text{ mA}$		-14.6	-14.4	V
		$I_L = 10\text{ mA}$ , $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		-14.3	-13.9	V
Output Short Circuit Current Limit	$I_{SC}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	$\pm 25$	$\pm 50$	$\pm 75$	mA
			$\pm 17$	$\pm 40$	$\pm 80$	mA
<b>POWER SUPPLY</b>						
Power Supply Rejection Ratio	PSRR	$\pm 2.5\text{ V} \leq V_S \leq \pm 18\text{ V}$	85	110		dB
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	80	105		dB
Supply Current/Amplifier	$I_{SY}$	$V_O = 0\text{ V}$		1.7	2.9	mA
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		1.75	3.0	mA
<b>DYNAMIC PERFORMANCE</b>						
Total Harmonic Distortion	THD	$R_L = 10\text{ k}\Omega$ , $f = 1\text{ kHz}$ , $V_O = 1\text{ V rms}$		0.0006		%
Slew Rate	SR	$R_L = 2\text{ k}\Omega$   50 pF	9	12		V/ $\mu\text{s}$
Gain Bandwidth Product	GBW			8		MHz
Channel Separation	CS	$R_L = 2\text{ k}\Omega$ , $f = 1\text{ kHz}$		128		dB
<b>NOISE PERFORMANCE</b>						
Voltage Noise Spectral Density	$e_n$	$f > 1\text{ kHz}$		8		nV/ $\sqrt{\text{Hz}}$
Current Noise Spectral Density	$i_n$	$f > 1\text{ kHz}$		< 1		pA/ $\sqrt{\text{Hz}}$

Specifications subject to change without notice.

**ELECTRICAL CHARACTERISTICS** ( $V_S = +5\text{ V}$ ,  $T_A = +25^\circ\text{C}$ ,  $V_{CM} = 2.5\text{ V}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>INPUT CHARACTERISTICS</b>						
Offset Voltage	$V_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		1	4	mV
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		1	6	nA
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		250	400	nA
Input Voltage Range	$V_{IN}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		300	500	nA
Common-Mode Rejection Ratio	CMRR	$+0.8\text{ V} \leq V_{CM} \leq +2\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	0.3	5	75	nA
$A_{VO}$		$R_L = 2\text{ k}\Omega$ , $-0.5\text{ V} \leq V_O \leq +4.5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	25	15	125	nA
			20	4.7		V
<b>OUTPUT CHARACTERISTICS</b>						
Output Voltage, High	$V_{OH}$	$I_L \leq -15\text{ mA}$ $I_L \leq -10\text{ mA}$ , $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	4.2	4.5		V
Output Voltage, Low	$V_{OL}$	$I_L \leq -15\text{ mA}$ $I_L \leq -10\text{ mA}$ , $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	4.5	4.8		V
Output Short Circuit Current Limit	$I_{SC}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		0.6	1.0	V
				0.3	0.5	V
				0.7	1.1	V
				40		mA
<b>POWER SUPPLY</b>						
Supply Current/Amplifier	$I_{SY}$	$V_O = 0\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		1.7	2.9	mA
				1.75	3.0	mA
<b>DYNAMIC PERFORMANCE</b>						
Total Harmonic Distortion	THD	$R_L = 10\text{ k}\Omega$ , $f = 1\text{ kHz}$ , $V_O = 1\text{ V rms}$		0.0006		%
Slew Rate	SR	$R_L = 2\text{ k}\Omega$   50 pF		12		V/ $\mu\text{s}$
Gain Bandwidth Product	GBW	$R_L = 2\text{ k}\Omega$   10 pF		6		MHz
Channel Separation	CS	$R_L = 2\text{ k}\Omega$ , $f = 1\text{ kHz}$		128		dB
<b>NOISE PERFORMANCE</b>						
Voltage Noise Spectral Density	$e_n$	$f > 1\text{ kHz}$		8		nV/ $\sqrt{\text{Hz}}$
Current Noise Spectral Density	$i_n$	$f > 1\text{ kHz}$		< 1		pA/ $\sqrt{\text{Hz}}$

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